Preferred Device

# **Complementary Darlington Power Transistors**

# **DPAK For Surface Mount Applications**

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, converters, and power amplifiers.

#### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series
- Pb-Free Packages are Available

#### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	100	Vdc
Collector-Base Voltage	V <sub>CB</sub>	100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current – Continuous – Peak	IC	2 4	Adc
Base Current	I <sub>B</sub>	50	mAdc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W W/°C
Total Power Dissipation (Note1)  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	71.4	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



#### ON Semiconductor®

http://onsemi.com

# SILICON POWER TRANSISTORS 2 AMPERES 100 VOLTS, 20 WATTS

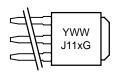
#### MARKING DIAGRAMS





DPAK CASE 369C





DPAK-3 CASE 369D

Y = Year WW = Work Week x = 2 or 7

G = Pb-Free Package

#### **ORDERING INFORMATION**

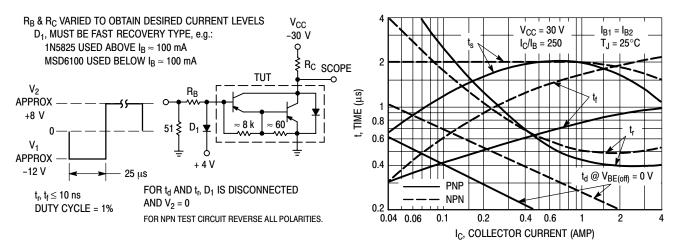
See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	
Collector–Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0)		V <sub>CEO(sus)</sub>	100	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 50 Vdc, I <sub>B</sub> = 0)		I <sub>CEO</sub>	_	20	μAdc
Collector Cutoff Current (V <sub>CB</sub> = 100 Vdc, I <sub>E</sub> = 0)		I <sub>CBO</sub>	_	20	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	_	2	mAdc
Collector–Cutoff Current (V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0)		I <sub>CBO</sub>	_	10	μAdc
Emitter–Cutoff Current $(V_{BE} = 5 \text{ Vdc}, I_C = 0)$		I <sub>EBO</sub>	_	2	mAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C=0.5 \text{ Adc, } V_{CE}=3 \text{ Vdc)} \\ (I_C=2 \text{ Adc, } V_{CE}=3 \text{ Vdc)} \\ (I_C=4 \text{ Adc, } V_{CE}=3 \text{ Vdc)} \end{array} $		h <sub>FE</sub>	500 1000 200	_ 12,000 _	-
Collector–Emitter Saturation Voltage ( $I_C = 2$ Adc, $I_B = 8$ mAdc) ( $I_C = 4$ Adc, $I_B = 40$ mAdc)		V <sub>CE(sat)</sub>	_ _	2 3	Vdc
Base-Emitter Saturation Voltage (I <sub>C</sub> = 4 Adc, I <sub>B</sub> = 40 mAdc)		V <sub>BE(sat)</sub>	_	4	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 2 Adc, V <sub>CE</sub> = 3 Vdc)		V <sub>BE(on)</sub>	-	2.8	Vdc
DYNAMIC CHARACTERISTICS				•	
Current–Gain – Bandwidth Product $(I_C = 0.75 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 1 \text{ MHz})$		f <sub>T</sub>	25	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	MJD117 MJD112	C <sub>ob</sub>	- -	200 100	pF

<sup>2.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s$ , Duty Cycle  $\leq 2\%$ . \*These ratings are applicable when surface mounted on the minimum pad sizes recommended.



**Figure 1. Switching Times Test Circuit** 

Figure 2. Switching Times

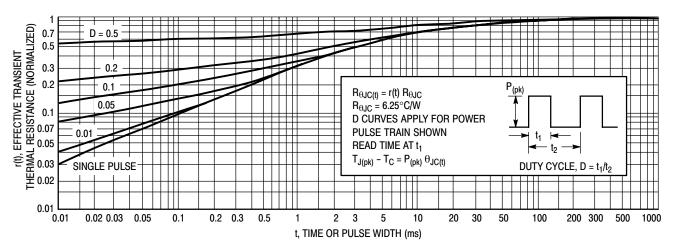


Figure 3. Thermal Response

#### **ACTIVE-REGION SAFE-OPERATING AREA**

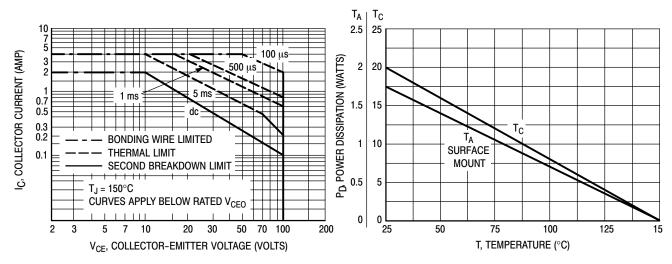
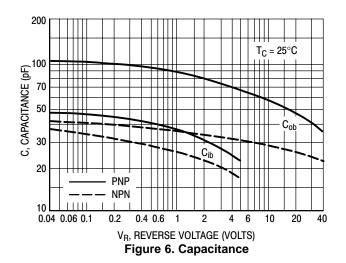


Figure 4. Maximum Rated Forward Biased Safe Operating Area

Figure 5. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5 and 6 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



#### TYPICAL ELECTRICAL CHARACTERISTICS

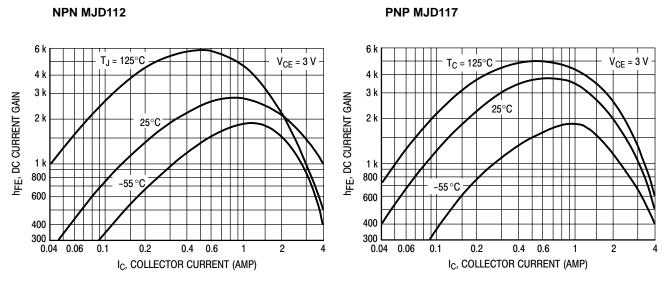


Figure 7. DC Current Gain

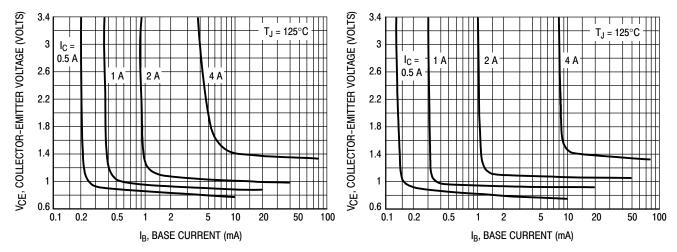


Figure 8. Collector Saturation Region

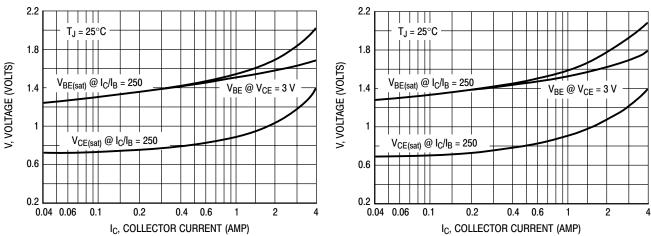


Figure 9. "On Voltages

NPN MJD112 PNP MJD117

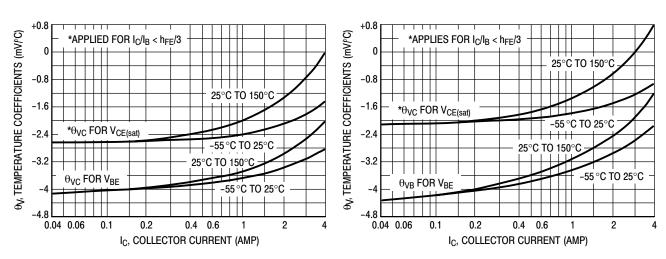


Figure 10. Temperature Coefficients

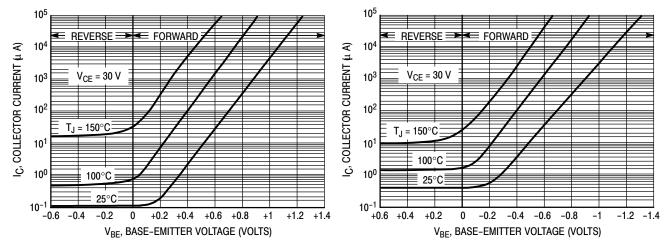


Figure 11. Collector Cut-Off Region

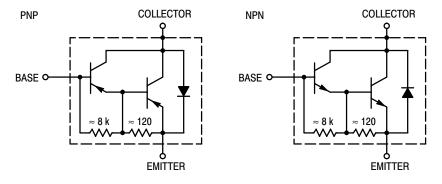


Figure 12. Darlington Schematic

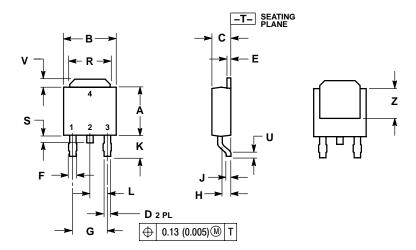
#### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>	
MJD112	DPAK		75 Unite / Dail	
MJD112G	DPAK (Pb-Free)	369C		
MJD112-001	DPAK-3		75 Units / Rail	
MJD112-1G	DPAK-3 (Pb-Free)	369D		
MJD112RL	DPAK		1800 Tape & Reel	
MJD112RLG	DPAK (Pb-Free)			
MJD112T4	DPAK		2500 Tape & Reel	
MJD112T4G	DPAK (Pb-Free)	369C		
MJD117	DPAK			
MJD117G	DPAK (Pb-Free)	1		
MJD117-001	DPAK-3		75 Units / Rail	
MJD117-1G	DPAK-3 (Pb-Free)	369D		
MJD117T4	DPAK			
MJD117T4G	DPAK (Pb-Free)	369C	2500 Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **PACKAGE DIMENSIONS**

#### **DPAK** CASE 369C **ISSUE O**

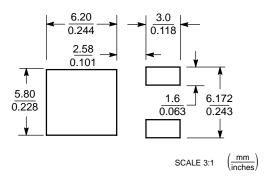


#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.22	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.180 BSC		4.58 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.102	0.114	2.60	2.89	
L	0.090 BSC		2.29 BSC		
R	0.180	0.215	4.57	5.45	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
٧	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

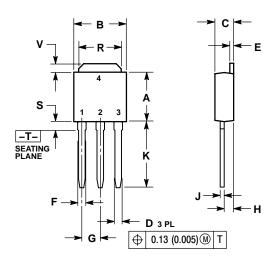
#### **SOLDERING FOOTPRINT\***

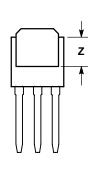


<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

DPAK-3 CASE 369D-01 **ISSUE B** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.090	BSC	2.29 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.350	0.380	8.89	9.65	
R	0.180	0.215	4.45	5.45	
S	0.025	0.040	0.63	1.01	
٧	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

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